

BD675G, BD675AG, BD677G, BD677AG, BD679G, BD679AG, BD681G

Plastic Medium-Power Silicon NPN Darlington

This series of plastic, medium-power silicon NPN Darlington transistors can be used as output devices in complementary general-purpose amplifier applications.

Features

- High DC Current Gain
- Monolithic Construction
- Complementary to BD676, 676A, 678, 678A, 680, 680A, 682
- BD677, 677A, 679, 679A are Equivalent to MJE 800, 801, 802, 803
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BD675G, BD675AG BD677G, BD677AG BD679G, BD679AG BD681G	V_{CEO}	45 60 80 100	Vdc
Collector-Base Voltage BD675G, BD675AG BD677G, BD677AG BD679G, BD679AG BD681G	V_{CBO}	45 60 80 100	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current	I_C	4.0	Adc
Base Current	I_B	1.0	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	40 0.32	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

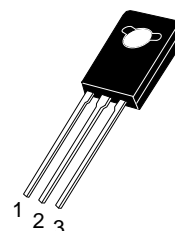
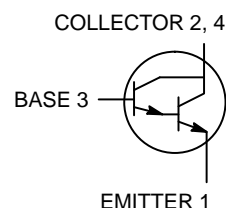
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.13	$^\circ\text{C}/\text{W}$



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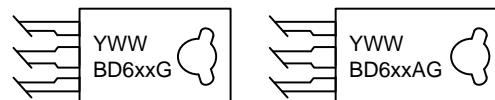
<http://onsemi.com>

**4.0 AMPERES
POWER TRANSISTORS
NPN SILICON
60, 80, 100 VOLTS, 40 WATTS**



TO-225
CASE 77-09
STYLE 1

MARKING DIAGRAMS



BD6xx/BD6xxA = Device Code
x = 75, 77, 79, 81
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BD675G, BD675AG, BD677G, BD677AG, BD679G, BD679AG, BD681G

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage, (Note 1) ($I_C = 50\text{ mAdc}$, $I_B = 0$) BD675G, BD675AG BD677G, BD677AG BD679G, BD679AG BD681G	BV_{CEO}	45 60 80 100	-	Vdc
Collector Cutoff Current ($V_{CE} = \text{Half Rated } BV_{CEO}$, $I_B = 0$)	I_{CEO}	-	500	μAdc
Collector Cutoff Current ($V_{CB} = \text{Rated } BV_{CEO}$, $I_E = 0$) ($V_{CB} = \text{Rated } BV_{CEO}$, $I_E = 0$, $T_C = 100^\circ\text{C}$)	I_{CBO}	-	0.2 2.0	mAdc
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	-	2.0	mAdc

ON CHARACTERISTICS

DC Current Gain, (Note 1) ($I_C = 1.5\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) BD675G, BD677G, BD679G, BD681G ($I_C = 2.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) BD675AG, BD677AG, BD679AG	h_{FE}	750 750	-	-
Collector-Emitter Saturation Voltage, (Note 1) ($I_C = 1.5\text{ Adc}$, $I_B = 30\text{ mAdc}$) BD677G, BD679G, BD681G ($I_C = 2.0\text{ Adc}$, $I_B = 40\text{ mAdc}$) BD675AG, BD677AG, BD679AG	$V_{CE(sat)}$	-	2.5 2.8	Vdc
Base-Emitter On Voltage, (Note 1) ($I_C = 1.5\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) BD677G, BD679G, BD681G ($I_C = 2.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) BD675AG, BD677AG, BD679AG	$V_{BE(on)}$	-	2.5 2.5	Vdc

DYNAMIC CHARACTERISTICS

Small Signal Current Gain ($I_C = 1.5\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$, $f = 1.0\text{ MHz}$)	h_{fe}	1.0	-	-
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Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

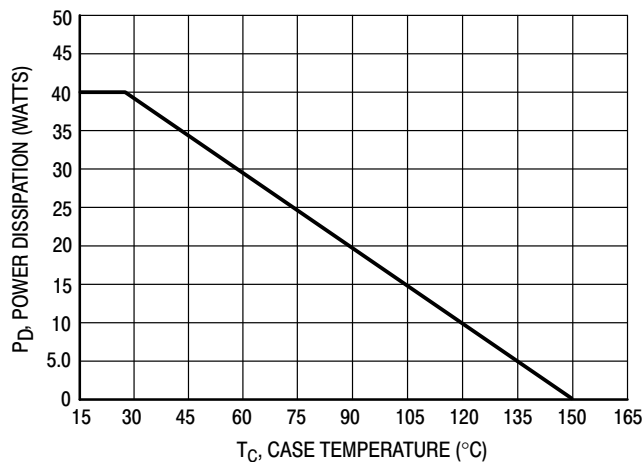


Figure 1. Power Temperature Derating

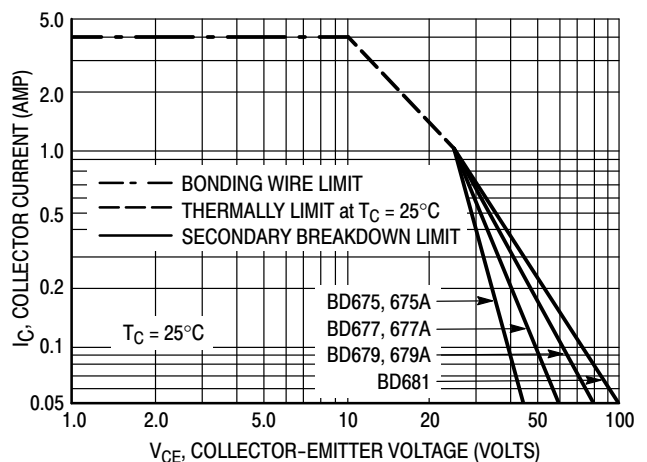


Figure 2. DC Safe Operating Area

BD675G, BD675AG, BD677G, BD677AG, BD679G, BD679AG, BD681G

There are two limitations on the power handling ability of a transistor average junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; e.g., the transistor must not be subjected to greater dissipation than the curves indicate.

At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by secondary breakdown.

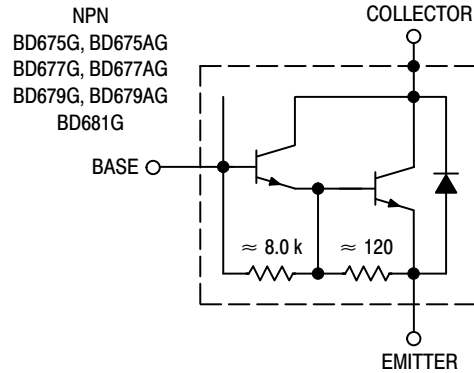


Figure 3. Darlington Circuit Schematic

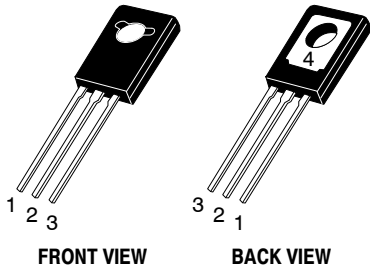
ORDERING INFORMATION

Device	Package	Shipping
BD675G	TO-225 (Pb-Free)	500 Units / Box
BD675AG	TO-225 (Pb-Free)	500 Units / Box
BD677G	TO-225 (Pb-Free)	500 Units / Box
BD677AG	TO-225 (Pb-Free)	500 Units / Box
BD679G	TO-225 (Pb-Free)	500 Units / Box
BD679AG	TO-225 (Pb-Free)	500 Units / Box
BD681G	TO-225 (Pb-Free)	500 Units / Box

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

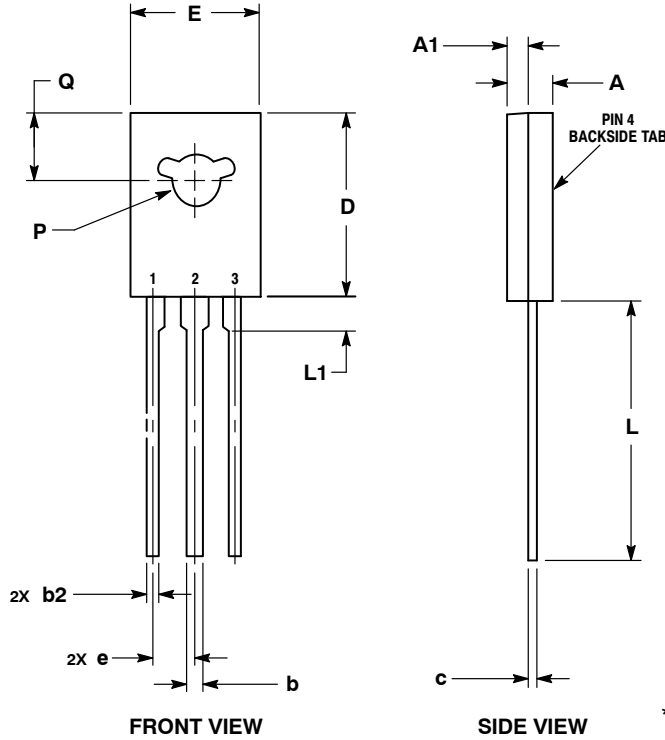
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CASE 77-09
ISSUE AD

DATE 25 MAR 2015

SCALE 1:1

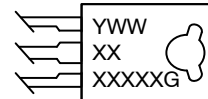


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. NUMBER AND SHAPE OF LUGS OPTIONAL.

DIM	MILLIMETERS	
	MIN	MAX
A	2.40	3.00
A1	1.00	1.50
b	0.60	0.90
b2	0.51	0.88
c	0.39	0.63
D	10.60	11.10
E	7.40	7.80
e	2.04	2.54
L	14.50	16.63
L1	1.27	2.54
P	2.90	3.30
Q	3.80	4.20

GENERIC MARKING DIAGRAM*



- Y = Year
- WW = Work Week
- XXXXX = Device Code
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present.

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|---|---|---|---|---|
| <p>STYLE 1:
PIN 1. EMITTER
2., 4. COLLECTOR
3. BASE</p> | <p>STYLE 2:
PIN 1. CATHODE
2., 4. ANODE
3. GATE</p> | <p>STYLE 3:
PIN 1. BASE
2., 4. COLLECTOR
3. EMITTER</p> | <p>STYLE 4:
PIN 1. ANODE 1
2., 4. ANODE 2
3. GATE</p> | <p>STYLE 5:
PIN 1. MT 1
2., 4. MT 2
3. GATE</p> |
| <p>STYLE 6:
PIN 1. CATHODE
2., 4. GATE
3. ANODE</p> | <p>STYLE 7:
PIN 1. MT 1
2., 4. GATE
3. MT 2</p> | <p>STYLE 8:
PIN 1. SOURCE
2., 4. GATE
3. DRAIN</p> | <p>STYLE 9:
PIN 1. GATE
2., 4. DRAIN
3. SOURCE</p> | <p>STYLE 10:
PIN 1. SOURCE
2., 4. DRAIN
3. GATE</p> |

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